



Ordering Information:

Absolute Maximum Ratings $T_C = 25$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	150	V
Gate-Source Voltage	V_{GS}	± 20	V
	$I_D @ T_C = 25^\circ C$	4.2	A

Continuous Drain Current

Thermal resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	R_{thJC}	-	-	34	$^{\circ}C/W$
Thermal resistance, junction - ambient	R_{thJA}	-	-	180	$^{\circ}C/W$
Soldering temperature, wavesoldering for 10s	T_{sold}	-	-	265	$^{\circ}C$

Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0V, I_D = 250\mu A$	150			V
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 250\mu A$	2.0		4.0	V
Drain-Source Leakage Current	I_{DSS}	$V_{DS} = 150V, V_{GS} = 0V$			1.0	μA
Gate- Source Leakage Current	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$			± 100	nA
Static Drain-source On Resistance		$V_{GS} = 10V, I_D = 20A$		60	78	m Ω
Forward Transconductance	g_{FS}	$V_{DS} = 10V, I_D = 20A$		4		s
Source-drain voltage	V_{SD}	$I_S = 20A$			1.28	V

Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Input capacitance	C_{iss}	f = 1MHz	-	1700	-	pF
Output capacitance	C_{oss}		-	85	-	
Reverse transfer capacitance	C_{rss}		-	49	-	

Gate Charge characteristics ($T_a = 25^{\circ}C$)

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Total gate charge						

Fig.1 Power Dissipation Derating Curve

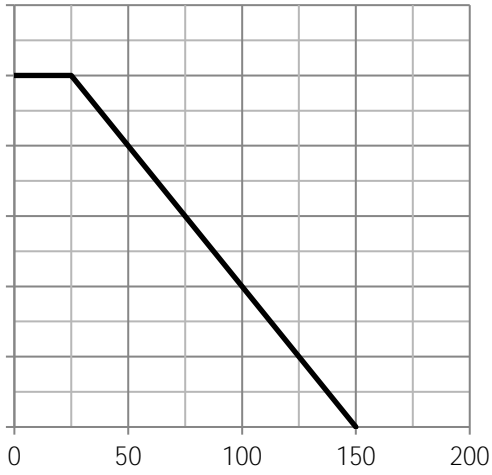


Fig.2 Typical output Characteristics

Fig.3 Threshold Voltage V.S Junction Temperature

Fig.4 Resistance V.S Drain Current



Fig.7 Switching Time Measurement Circuit

Fig.8 Gate Charge Waveform

Fig.9 Switching Time Measurement Circuit

Fig.10 Gate Charge Waveform

Fig.11 Avalanche Measurement Circuit

Fig.12 Avalanche Waveform

Dimensions(SOP8)

Unit: mm

SYMBOL	min	TYP	max	SYMBOL	min		max
A	4.80		5.25	C	1.30		1.75
A1	0.37		0.49	C1	0.55		0.75
A2		1.27		C2	0.55		0.65
A3		0.41		C3	0.05		0.20
B	5.80		6.20	C4	0.10	0.20	0.23
B1	3.80		4.10	D		1.05	
B2		5.00		D1	0.40		0.62

